BLL6H1214L-250; BLL6H1214LS-250 LDMOS L-band radar power transistor

AMMPLEON

Rev. 4 — 1 September 2015

Product data sheet

Product profile 1.

1.1 General description

250 W LDMOS power transistor intended for L-band radar applications in the 1.2 GHz to 1.4 GHz range.

Table 1. **Test information**

Typical RF performance at $T_{case} = 25$ °C; $t_D = 300 \ \mu s$; $\delta = 10 \%$; $I_{Dq} = 100 \ mA$; in a class-AB production test circuit.

Mode of operation	f	V _{DS}	P _L	Gp	η_{D}	t _r	t _f
	(GHz)	(V)	(W)	(dB)	(%)	(ns)	(ns)
pulsed RF	1.2 to 1.4	50	250	17	55	15	5

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features and benefits

- Typical pulsed RF performance at a frequency of 1.2 GHz to 1.4 GHz, a supply voltage of 50 V, an I_{Da} of 100 mA, a t_p of 300 μs with δ of 10 %:
 - ◆ Output power = 250 W
 - ◆ Power gain = 17 dB
 - ◆ Efficiency = 55 %
- Easy power control
- Integrated ESD protection
- High flexibility with respect to pulse formats
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (1.2 GHz to 1.4 GHz)
- Internally matched for ease of use
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

1.3 Applications

■ L-band power amplifiers for radar applications in the 1.2 GHz to 1.4 GHz frequency range

2. Pinning information

Table 2. Pinning

Table 2.	Filling		
Pin	Description	Simplified outline	Graphic symbol
BLL6H12	14L-250 (SOT502A)		
1	drain		
2	gate		
3	source	[1] 5 3	2
		2	3 sym112
BI I 6H12	14LS-250 (SOT502B)		
DELOTTIZ			
1	drain		4
2	gate	1	نے
3	source	[1]	2
		2	3
			sym112

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BLL6H1214L-250	-	flanged LDMOST ceramic package; 2 mounting holes; 2 leads	SOT502A			
BLL6H1214LS-250	-	earless flanged LDMOST ceramic package; 2 leads	SOT502B			

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	100	V
V_{GS}	gate-source voltage		-0.5	+13	V
I_D	drain current		-	42	Α
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	200	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
Z _{th(j-c)} transient thermal impedance from junction to case	•	T_{case} = 85 °C; P_{L} = 250 W		
	t_p = 100 μ s; δ = 10 %	0.10	K/W	
	t_p = 200 μ s; δ = 10 %	0.13	K/W	
	t_p = 300 μ s; δ = 10 %	0.15	K/W	
	t_p = 100 μ s; δ = 20 %	0.14	K/W	
		t_p = 500 μ s; δ = 20 %	0.20	K/W

6. Characteristics

Table 6. DC characteristics

 $T_i = 25 \, ^{\circ}\text{C}$.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.7 \text{ mA}$	100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_{D} = 270 mA	1.3	1.8	2.25	V
I _{DSS}	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$	-	-	1.4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	32	42	-	Α
I_{GSS}	gate leakage current	$V_{GS} = 11 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	140	nA
g _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 270 mA	1.6	2.3	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 9.5 \text{ A}$	-	100	169	mΩ

Table 7. RF characteristics

Mode of operation: pulsed RF; t_p = 300 μ s; δ = 10 %; RF performance at V_{DS} = 50 V; I_{Dq} = 100 mA; T_{case} = 25 °C; unless otherwise specified, in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
P_L	output power		250	-	-	W
V_{DS}	drain-source voltage	P _L = 250 W	-	-	50	V
Gp	power gain	$P_{L} = 250 \text{ W}$	15	17	-	dB
t _p	pulse duration	$P_{L} = 250 \text{ W}$	-	300	500	μS
δ	duty cycle	$P_{L} = 250 \text{ W}$	-	10	20	%
RLin	input return loss	$P_{L} = 250 \text{ W}$	-	10	-	dB
P _{L(1dB)}	output power at 1 dB gain compression		-	300	-	W
η_{D}	drain efficiency	$P_{L} = 250 \text{ W}$	49	55	-	%
P _{droop(pulse)}	pulse droop power	$P_{L} = 250 \text{ W}$	-	0	0.3	dB
t _r	rise time	$P_{L} = 250 \text{ W}$	-	15	-	ns
t_f	fall time	$P_{L} = 250 \text{ W}$	-	5	-	ns

6.1 Ruggedness in class-AB operation

The BLL6H1214L-250 and BLL6H1214LS-250 are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 50 V; I_{Dq} = 100 mA; P_L = 250 W; t_p = 300 μ s; δ = 10 %.

7. Application information

7.1 Impedance information

Table 8. Typical impedance *Typical values unless otherwise specified.*

f	Z _S	Z_L
GHz	Ω	Ω
1.2	1.268 – j2.623	2.987 – j1.664
1.3	2.193 – j2.457	2.162 – j1.326
1.4	2.359 – j2.052	1.604 – j1.887

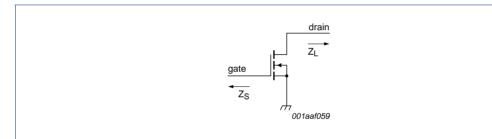
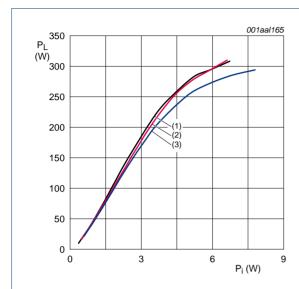


Fig 1. Definition of transistor impedance

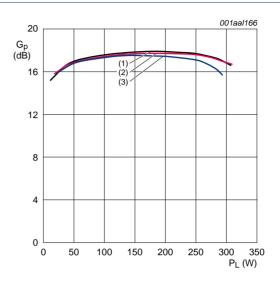
7.2 RF performance



 V_{DS} = 50 V; t_p = 300 $\mu s;~\delta$ = 10 %; I_{Dq} = 100 mA.

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

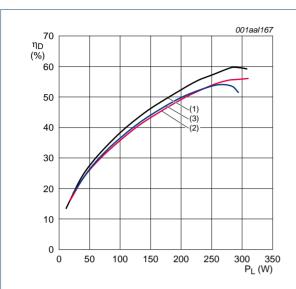
Fig 2. Output power as a function of input power; typical values



 V_{DS} = 50 V; t_p = 300 μs ; δ = 10 %; I_{Dq} = 100 mA.

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

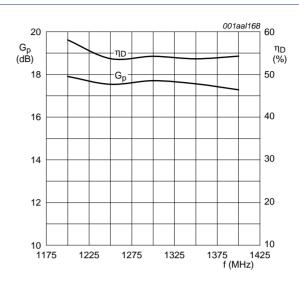
Fig 3. Power gain as a function of load power; typical values



$$V_{DS}$$
 = 50 V; t_p = 300 μs ; δ = 10 %; I_{Dq} = 100 mA.

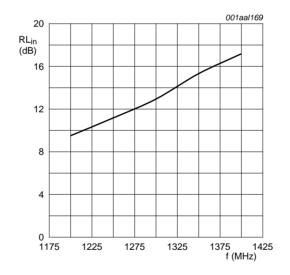
- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

Fig 4. Drain efficiency as a function of load power; typical values



$$P_L$$
 = 250 W; V_{DS} = 50 V; t_p = 300 $\mu s;~\delta$ = 10 %; I_{Dq} = 100 mA.

Fig 5. Power gain and drain efficiency as function of frequency; typical values



 P_L = 250 W; V_{DS} = 50 V; t_p = 300 $\mu s;$ δ = 10 %; I_{Dq} = 100 mA.

Fig 6. Input return loss as a function of frequency; typical value

7.3 Application circuit

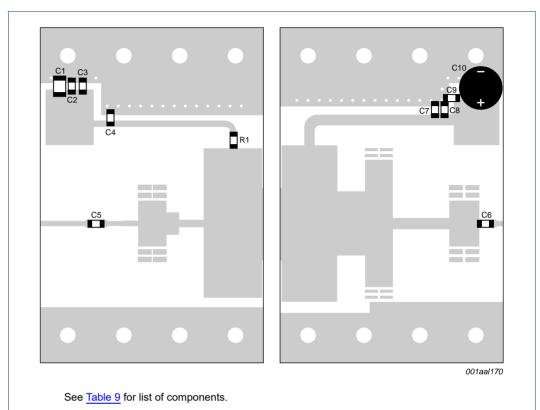


Fig 7. Component layout for class-AB application circuit

Table 9. List of components

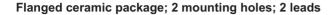
See Figure 7.

Striplines are on a Rodgers Duroid 6006 Printed-Circuit Board (PCB); $\varepsilon_r = 6.15$ F/m; thickness = 0.64 mm

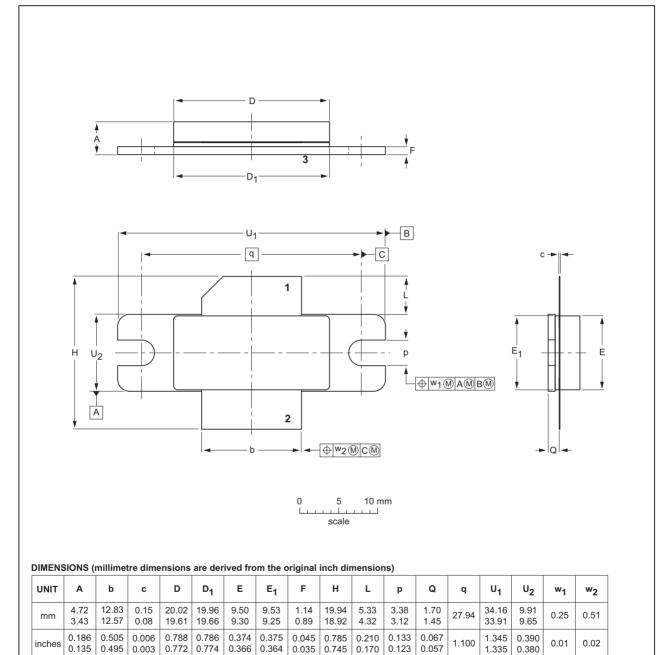
Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	10 μF; 35 V	[1]
C2, C4	multilayer ceramic chip capacitor	51 pF	[2]
C3, C8	multilayer ceramic chip capacitor	1 nF	[2]
C5	multilayer ceramic chip capacitor	82 pF	[3]
C6, C7	multilayer ceramic chip capacitor	56 pF	[3]
C9	multilayer ceramic chip capacitor	100 pF	[3]
C10	electrolytic capacitor	47 μF; 63 V	
R1	SMD resistor	10 Ω	0603

- [1] American Technical Ceramics type 100A or capacitor of same quality.
- [2] American Technical Ceramics type 100B or capacitor of same quality.
- [3] American Technical Ceramics type 800B or capacitor of same quality.

8. Package outline



SOT502A

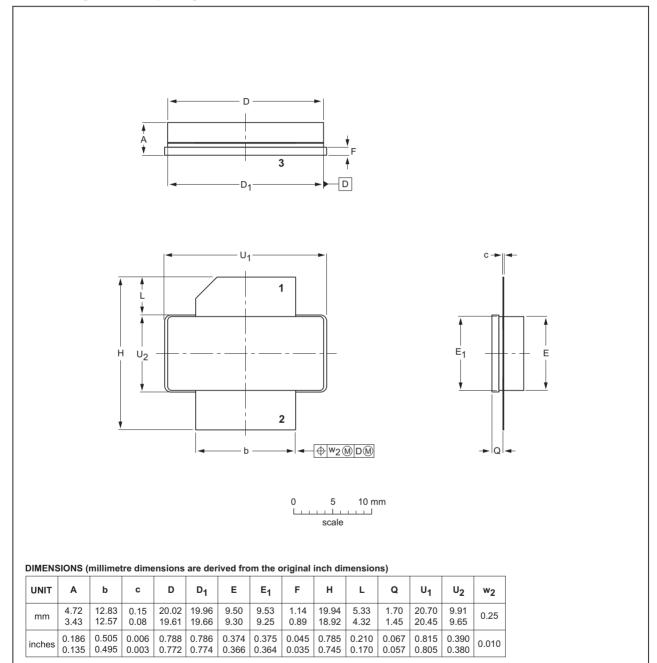


OUTLINE REFERENCES					EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT502A						-03-01-10 12-05-02

Fig 8. Package outline SOT502A

Earless flanged ceramic package; 2 leads

SOT502B



OUTLINE		REFERENCES EUROPEAN		ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT502B					-07-05-09 12-05-02

Fig 9. Package outline SOT502B

9. Abbreviations

Table 10. Abbreviations

Acronym	Description
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LDMOST	Laterally Diffused Metal-Oxide Semiconductor Transistor
RF	Radio Frequency
SMD	Surface Mounted Device
VSWR	Voltage Standing-Wave Ratio

10. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLL6H1214L-250_1214LS-250#4	20150901	Product data sheet		BLL6H1214L-250_1214LS-250#3	
Modifications:		rmat of this documer nes of Ampleon.	it has been redesig	ned to comply with the new identity	
	Legal texts have been adapted to the new company name where appropriate.				
BLL6H1214L-250_1214LS-250#3	20100714	Product data sheet	-	BLL6H1214L-250_1214LS-250#2	
BLL6H1214L-250_1214LS-250#2	20100302	Objective data sheet	-	BLL6H1214L-250_1214LS-250#1	
BLL6H1214L-250_1214LS-250#1	20091211	Objective data sheet	-	-	

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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LDMOS L-band radar power transistor

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LDMOS L-band radar power transistor

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